C1

a second interconnect selectively provided on the second interlayer insulating film and electrically connected to the first interconnect through a second contact hole formed in the second interlayer insulating film; and

a passivation layer provided so as to cover the second interconnect.

30. (Amended) A semiconductor device, comprising:

a capacitor provided on a supporting substrate having an integrated circuit thereon and including a lower electrode, a dielectric film, and an upper electrode, said dielectric film including a remnant polarization of approximately 10 $\mu C/cm^2$;

a first interlayer insulating film provided so as to directly cover the capacitor;

a first interconnect selectively provided on the first interlayer insulating film and electrically connected to the integrated circuit and the capacitor through a first contact hole formed in the first interlayer insulating film;

C2

a second interlayer insulating film having a tensile stress provided so as to directly cover the first interconnect and the first interlayer insulating film;

a second interconnect selectively provided on the second interlayer insulating film and electrically connected to the first interconnect through a second contact hole formed in the second interlayer insulating film; and

a passivation layer provided so as to cover the second interconnect.

31. (Amended) A semiconductor device, comprising:

a capacitor provided on a supporting substrate having an integrated circuit thereon and including a lower electrode, a dielectric film, and an upper electrode, said dielectric film including a remnant polarization of at least 10 $\mu C/cm^2$;

a first interlayer insulating film provided so as to directly cover the capacitor;

a first interconnect selectively provided on the first interlayer insulating film and electrically connected to the integrated circuit and the capacitor through a first contact hole formed in the first interlayer insulating film;

a second interlayer insulating film having a tensile stress provided so as to directly cover the first interconnect and the first interlayer insulating film;

a second interconnect selectively provided on the second interlayer insulating film and electrically connected to the first interconnect through a second contact hole formed in the second interlayer insulating film; and

a passivation layer provided so as to cover the second interconnect.

Please cancel claim 2.

Please add claim 32.

32. (Newly Added) A semiconductor device, comprising:

a capacitor provided on a supporting substrate having an integrated circuit thereon and including a lower electrode, a dielectric film, and an upper electrode;

a first interlayer insulating film provided so as to directly cover the capacitor, the first interlayer insulating film having a tensile stress;

a first interconnect selectively provided on the first interlayer insulating film and electrically connected to the integrated circuit and the capacitor through a first contact hole formed in the first interlayer insulating film;

a second interlayer insulating film having a tensile stress provided so as to directly cover the first interconnect and the first interlayer insulating film;

a second interconnect selectively provided on the second interlayer insulating film and electrically connected to the first interconnect through a second contact hole formed in the second interlayer insulating film; and

a ~~passivation~~ layer provided so as to cover the second interconnect.